



DC COMPONENTS CO., LTD.

RECTIFIER SPECIALISTS

1N60P

TECHNICAL SPECIFICATIONS OF SMALL SIGNAL SCHOTTKY DIODES

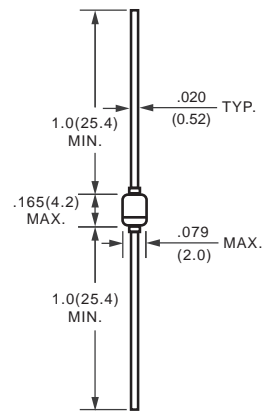
FEATURES

- \* Metal silicon junction, majority carrier conduction.
- \* High current capability, low forward voltage drop.
- \* Extremely low reverse current  $I_r$
- \* Ultra speed switching characteristics
- \* Small temperature coefficient of forward characteristics
- \* Satisfactory Wave detection efficiency
- \* For use in RECORDER, TV, RADIO, TELEPHONE as detectors, super high speed switching circuits, small current rectifier

MECHANICAL DATA

- \* Case: DO-35 glass case
- \* Polarity: color band denotes cathode end
- \* Weight: 0.13 grams approx.

DO-35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.  
Single phase, half wave, 60 Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

ABSOLUTE RATINGS(LIMITING VALUES)

PARAMETERS	SYMBOL	VALUE	UNITS
ZeneRepetitive Peak Reverse Voltage	$V_{RRM}$	45	Volts
Forward Continuous Current	$I_F$	50	mA
Peak Forward Surge Current(t=1S)	$I_{FSM}$	500	mA
Storage and junction Temperature Range	$T_{STG}/T_J$	-65 to +125	°C
Maximum Lead Temperature for Soldering during 10S at 4mm from Case	$T_L$	230	°C

ELECTRICAL CHARACTERISTICS

PARAMETERS	TEST CONDITIONS	SYMBOL	VALUE		UNITS
			TYP.	MAX.	
Forward Voltage	$I_F=1mA$	$V_F$	0.24	0.5	Volts
	$I_F=200mA$		0.65	1.0	
Reverse Current	$V_R=15V$	$I_R$	0.5	1.0	μA
Junction Capacitance	$V_R=10V$ $f=1MHz$	$C_J$	6.0		pF
Detection Efficiency	$V_I=3V$ $f=30MHz$ $C_L=10pF$ $R_L=3.8K\Omega$	$\eta$	60		%
Reverse Recovey time	$I_F=I_R=1mA$ $I_{rr}=1mA$ $R_C=100\Omega$	$t_{rr}$		1	ns
Junction Ambient Thermal Resistance		$R_{\theta JA}$	400		°C/W

# RATING AND CHARACTERISTIC CURVES 1N60P

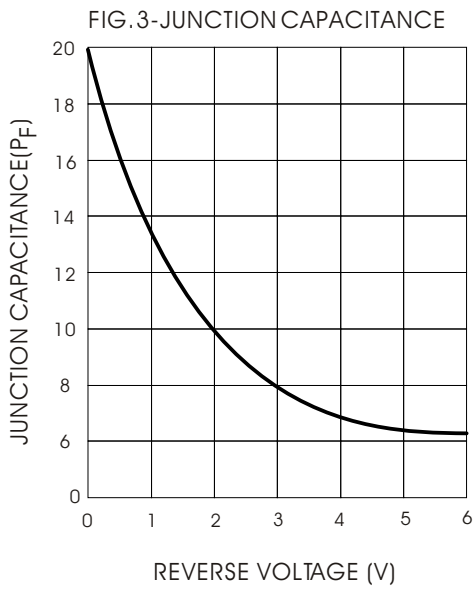
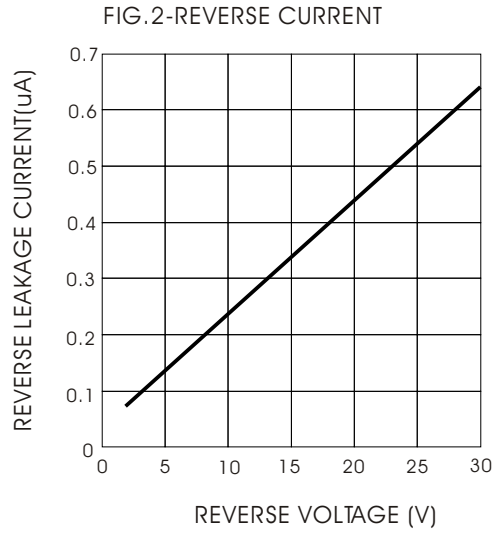
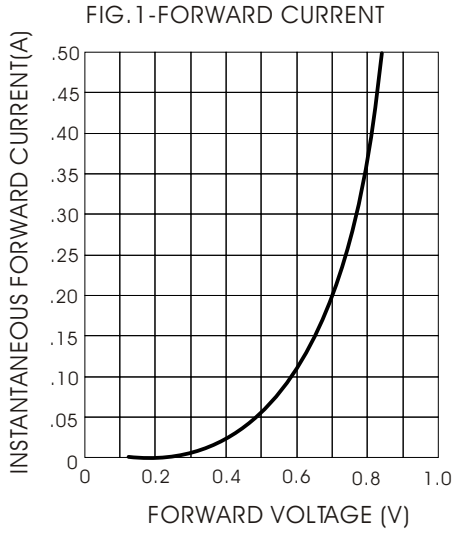


FIG. 4-DETECTION EFFICIENCY MEASUREMENT CIRCUIT

